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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/540,515	06/23/2005	Tsuyoshi Nakano	Q88663	6621
23373	7590	01/24/2006	EXAMINER	
SUGHRUE MION, PLLC 2100 PENNSYLVANIA AVENUE, N.W. SUITE 800 WASHINGTON, DC 20037				HARRISON, MONICA D
			ART UNIT	PAPER NUMBER
			2813	

DATE MAILED: 01/24/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No.	Applicant(s)	
	10/540,515	NAKANO ET AL.	
	Examiner	Art Unit	
	Monica D. Harrison	2813	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

1) Responsive to communication(s) filed on 23 June 2005.
 2a) This action is FINAL. 2b) This action is non-final.
 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

4) Claim(s) 1-8 is/are pending in the application.
 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
 5) Claim(s) _____ is/are allowed.
 6) Claim(s) 1-8 is/are rejected.
 7) Claim(s) _____ is/are objected to.
 8) Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

9) The specification is objected to by the Examiner.
 10) The drawing(s) filed on 23 June 2005 is/are: a) accepted or b) objected to by the Examiner.
 Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
 Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
 a) All b) Some * c) None of:
 1. Certified copies of the priority documents have been received.
 2. Certified copies of the priority documents have been received in Application No. _____.
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

1) Notice of References Cited (PTO-892)
 2) Notice of Draftsperson's Patent Drawing Review (PTO-948)
 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
 Paper No(s)/Mail Date 6-23-05 9/20/05

4) Interview Summary (PTO-413)
 Paper No(s)/Mail Date. _____.
 5) Notice of Informal Patent Application (PTO-152)
 6) Other: _____

DETAILED ACTION

Priority

1. Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1-8 are rejected under 35 U.S.C. 102(b) as being anticipated by Johnson et al (6,429,103 B1).

2. Regarding claim 1, Johnson et al discloses a semiconductor epitaxial substrate for use a pseudomorphic high electron mobility field effect transistor, comprising an InGaAs layer as a channel layer (Figure 3, reference 20) and an InGaP layer containing n-type impurities as a front side electron supplying layer (Figure 3, reference 11; column 2, lines 52-56), said InGaAs layer having an electron mobility at room temperature (300 K) of 8000 cm²/Vs or more (Figure 2).

3. Regarding claim 2, Johnson et al discloses an InGaP layer as a front side spacer layer between said channel layer and said front side electron supplying layer (Figure 3, reference 11).

4. Regarding claim 3, Johnson et al discloses an InGaP layer containing n-type impurities also as a back side electron supplying layer and comprising an InGaP layer as a back

side spacer layer between said channel layer and said back side electron supplying layer (Figure 3).

5. Regarding claim 4, Johnson et al discloses wherein an In composition of the InGaAs layer constituting of said channel layer is 0.25 or more (Figure 3, reference 20).

6. Regarding claim 5, Johnson et al discloses wherein GaAs layers each of which has a thickness of 4 nm or more are laminated on said channel layer in contact with a top surface and a bottom surface of said channel layer, respectively (column 2, lines 42-51).

7. Regarding claim 6, Johnson et al discloses that an epitaxial layer of each compound semiconductor is formed by employing an MOCVD method (column 1, lines 54-67 thru column 2, lines 1-9).

8. Regarding claim 7, Johnson et al discloses that an epitaxial layer of each compound semiconductor is formed by employing an MOCVD method (column 1, lines 54-67 thru column 2, lines 1-9).

9. Regarding claim 8, Johnson et al discloses that an epitaxial layer of each compound semiconductor is formed by employing an MOCVD method (column 1, lines 54-67 thru column 2, lines 1-9).

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Monica D. Harrison whose telephone number is 571-272-1959. The examiner can normally be reached on M-F 7:00am-3:30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead Jr. can be reached on 571-272-1702. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Monica D. Harrison
AU 2813

mdh
January 20, 2006



LAURA M. SCHILLINGER
PRIMARY EXAMINER